

BCW65ALT1, BCW65CLT1

General Purpose Transistor

NPN Silicon

Features

- Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emmitter Voltage	V_{CEO}	32	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current - Continuous	I_C	800	mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

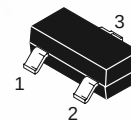
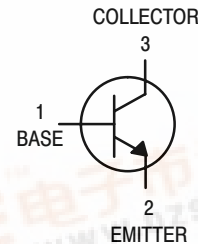
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1), $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

- FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.



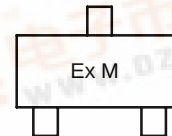
ON Semiconductor®

<http://onsemi.com>



SOT-23
CASE 318
STYLE 6

MARKING DIAGRAM



EA = Specific Device Code (BCW65ALT1)
EC = Specific Device Code (BCW65CLT1)
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
BCW65ALT1	SOT-23	3000 / Tape & Reel
BCW65ALT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BCW65CLT1	SOT-23	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BCW65ALT1, BCW65CLT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = 10\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	32	–	–	Vdc
Collector–Emitter Breakdown Voltage ($I_C = 10\text{ }\mu\text{Adc}$, $V_{EB} = 0$)	$V_{(BR)CES}$	60	–	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	5.0	–	–	Vdc
Collector Cutoff Current ($V_{CE} = 32\text{ Vdc}$, $I_E = 0$) ($V_{CE} = 32\text{ Vdc}$, $I_E = 0$, $T_A = 150^\circ\text{C}$)	I_{CES}	– –	– –	20 20	nAdc μAdc
Emitter Cutoff Current ($V_{EB} = 4.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	–	20	nAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 100\text{ }\mu\text{Adc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 100\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 500\text{ mAdc}$, $V_{CE} = 2.0\text{ Vdc}$)	BCW65ALT1	h_{FE}	35 75 100 35	– – – –	– – 250 –	–
DC Current Gain ($I_C = 100\text{ }\mu\text{Adc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 100\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 500\text{ mAdc}$, $V_{CE} = 2.0\text{ Vdc}$)	BCW65CLT1	h_{FE}	80 180 250 100	– – – –	– – 630 –	–
Collector–Emitter Saturation Voltage ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$) ($I_C = 100\text{ mAdc}$, $I_B = 10\text{ mAdc}$)		$V_{CE(sat)}$	– –	0.7 0.3	– –	Vdc
Base–Emitter Saturation Voltage ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$)		$V_{BE(sat)}$	–	–	2.0	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 20\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	–	–	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	–	–	12	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	–	–	80	pF
Noise Figure ($V_{CE} = 5.0\text{ Vdc}$, $I_C = 0.2\text{ mAdc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	NF	–	–	10	dB

SWITCHING CHARACTERISTICS

Turn–On Time ($I_{B1} = I_{B2} = 15\text{ mAdc}$)	t_{on}	–	–	100	ns
Turn–Off Time ($I_C = 150\text{ mAdc}$, $R_L = 150\text{ }\Omega$)	t_{off}	–	–	400	ns

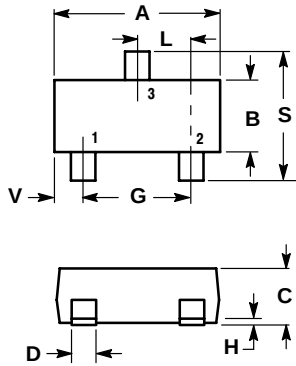
BCW65ALT1, BCW65CLT1

PACKAGE DIMENSIONS

SOT-23 (TO-236)

CASE 318-08

ISSUE AK



NOTES:

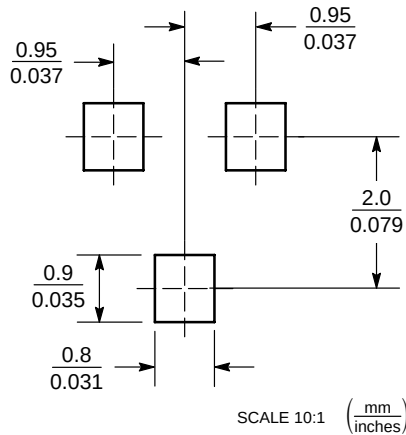
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 6:

- PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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